

GaAs HIGH POWER SIDE LOOK PACKAGE INFRARED EMITTING DIODE

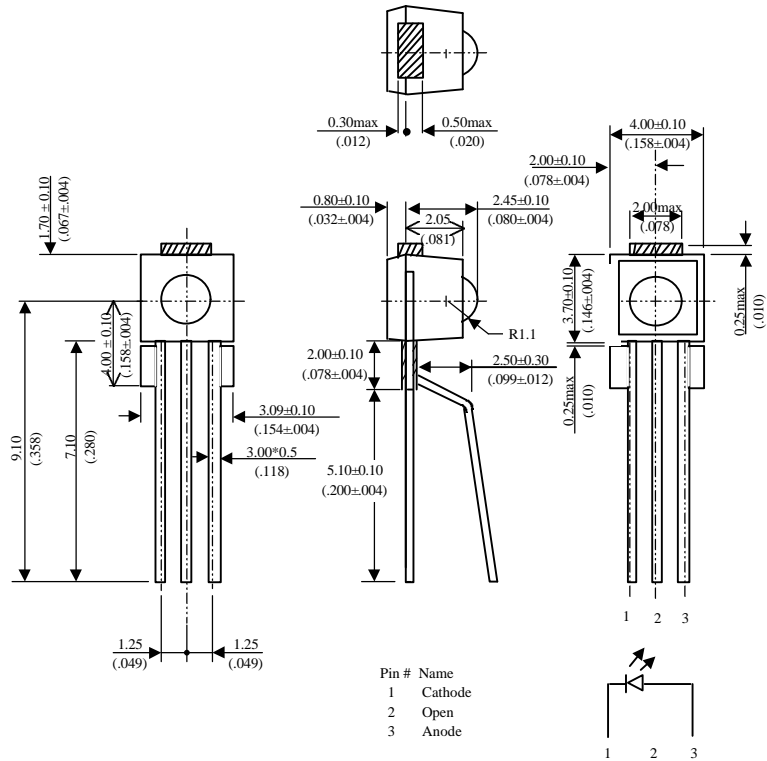
MIE-134A1-02

Description

The MIE-134A1-02 is a GaAs infrared emitting diode molded in clear, lensed side looking package. The MIE-134A1-02 provides a broad range of intensity selection .

Package Dimensions

Unit: mm(inches)



Features

- Selected to specific on-line intensity and radiant intensity ranges
- Low cost, plastic side looking package
- Mechanically and spectrally matched to The MID-13A45 of phototransistor .

NOTES :

- All dimensions are in millimeters.(inches).
- Tolerance is ± 0.25mm (.010") unless otherwise noted .
- Lead spacing is measured where the leads emerge from the package.

Absolute Maximum Ratings

@ T_A=25°C

Parameter	Maximum Rating	Unit
Power Dissipation	75	mW
Peak Forward Current	1	A
Continuous Forward Current	50	mA
Reverse Voltage	5	V
Operating Temperature Range	-55°C to +100°C	
Storage Temperature Range	-55°C to +100°C	
Lead Soldering Temperature	260°C for 5 seconds	

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12/23/1999

Optical-Electrical Characteristics

@ T_A=25°C

Parameter	Test Conditions	Symbol	Min.	Typ .	Max.	Unit
Radiant Incidance	I _F =20mA	E _e	-	1.2	-	mW/cm ²
Forward Voltage	I _F =20mA	V _F	-	1.25	1.35	V
Reverse Current	V _R =5V	I _R	-	-	100	μA
Peak Wavelength	I _F =20mA	λ	-	940	-	nm
Spectral Bandwidth	I _F =20mA	Δλ	-	50	-	nm
View Angle	I _F =20mA	2θ _{1/2}	-	30	-	deg .

Typical Optical-Electrical Characteristic Curves

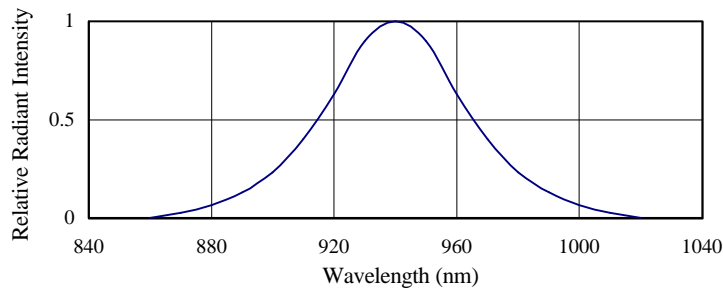


FIG.1 SPECTRAL DISTRIBUTION

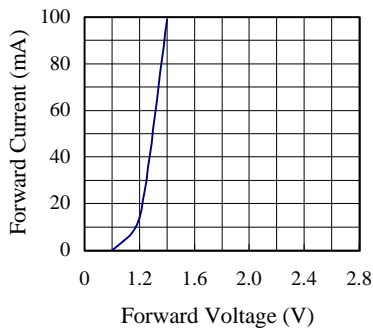


FIG.2 FORWARD CURRENT VS. FORWARD VOLTAGE

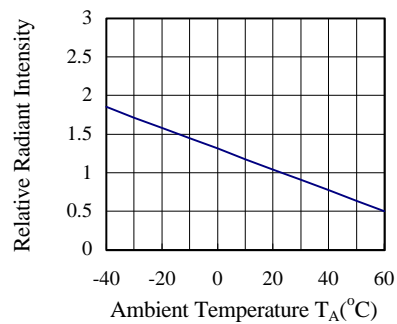


FIG.3 RELATIVE RADIANT INTENSITY VS. AMBIENT TEMPERATURE

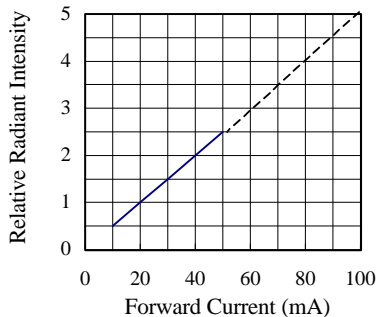


FIG.4 RELATIVE RADIANT INTENSITY VS. FORWARD CURRENT

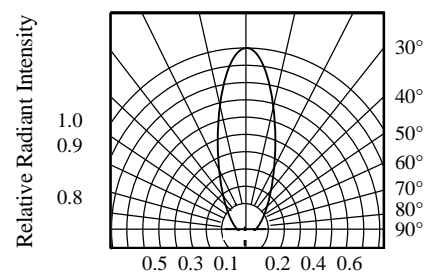


FIG.5 RADIATION DIAGRAM